风光欣技术资料

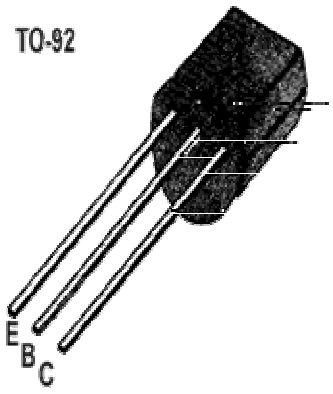
2N2222

—NPN silicon —

APPLICATION：General Purpose Amplifier Application.

MAXIMUM RATING（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	600	mA
Collector Power Dissipation	P_C	600	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



ELECTRICAL CHARACTERISTICS（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h_{FE}	100		300		V_{CE}= 10V，Ic= 150mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 50 V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 5 V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	60			V	Ic= 0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	30			V	Ic= 1 mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E= 0.1mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.4	V	Ic= 150 mA，I_B= 15 mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.3	V	Ic= 150 mA, I_B= 15 mA
Gain bandwidth product	f_T	250			MHz	Ic= 20 mA，V_{CE}= 20 V
Common Base Output Capacitance	Cob			8	PF	V_{CB}= 10 V, I_E=0, f = 1 MHz
Turn on Time	t_{on}			35	dB	Vcc= 30 V，Ic= 150 mA, I_{B1}=15mA
Turn off Time	t_{off}			285	dB	Vcc= 30 V，Ic= 150 mA, I_{B1}=I_{B2}=15mA

h_{FE} Classification

Classification	
h_{FE}	100 ～300